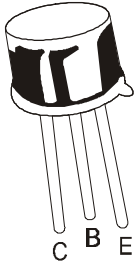


NPN SILICON PLANAR EPITAXIAL TRANSISTORS

**2N3019
2N3020**

**TO-39
Metal Can Package**



**Designed for use in General Purpose Amplifier and High Speed Switching Applications
These Transistors are also Suitable for High Current Amplifier Applications**

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	V_{CEO}	80	V
Collector Base Voltage	V_{CBO}	140	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current	I_{CM}	1	A
Power Dissipation @ Ta=25° C	P_D	800	mW
Power Dissipation @ Tc=25°C		5	W
Junction Temperature	T_j	+200	°C
Storage Temperature	T_{stg}	-65 to +200	°C
THERMAL RESISTANCE			
Junction to Ambient	$R_{th(j-a)}$	218.7	°C/W
Junction to Case	$R_{th(j-c)}$	35	°C/W

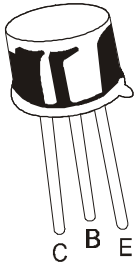
ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Collector Emitter Breakdown Voltage	BV_{CEO}^*	$I_C=30mA, I_B=0$	80		V
Collector Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	140		V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu A, I_C=0$	7		V
Collector Leakage Current	I_{CBO}	$V_{CB}=90V, I_E=0$		10	nA
		$V_{CB}=90V, I_E=0, T_a=150^\circ C$		10	μA
Emitter Leakage Current	I_{EBO}	$V_{EB}=5V, I_C=0$		10	nA
Collector Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C=150mA, I_B=15mA$		0.2	V
		$I_C=500mA, I_B=50mA$		0.5	V
Base Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C=150mA, I_B=15mA$		1.1	V

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ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

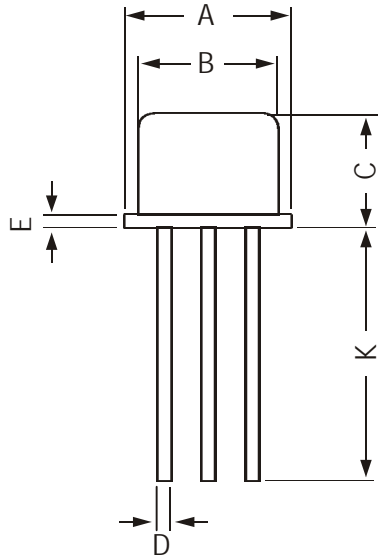
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
DC Current Gain	h_{FE}^*	$I_C=0.1mA, V_{CE}=10V$			
2N3019			50		
2N3020			30	100	
	h_{FE}^*	$I_C=10mA, V_{CE}=10V$			
2N3019			90		
2N3020			40	120	
	h_{FE}^*	$I_C=150mA, V_{CE}=10V$			
2N3019			100	300	
2N3020			40	120	
	h_{FE}^*	$I_C=500mA, V_{CE}=10V$			
2N3019			50		
2N3020			30	100	
	h_{FE}^*	$I_C=1A, V_{CE}=10V$			
2N3019			15		
2N3020			15		
	h_{FE}^*	$I_C=150mA, V_{CE}=10V$ $T_C = -55^\circ C$			
2N3019			40		
SMALL SIGNAL CHARACTERISTICS					
Small Signal Current Gain	$ h_{fe} $	$I_C=1mA, V_{CE}=5V, f=1KHz$			
2N3019			80	400	
2N3020			30	200	
Transition Frequency	f_T	$I_C=50mA, V_{CE}=10V$			
2N3019		$f=20MHz$	100		MHz
2N3020			80		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		12	pF
Input Capacitance	C_{ib}	$V_{EB}=0.5V, I_C=0, f=1MHz$		60	pF
Noise Figure	NF	$I_C=100\mu A, V_{CE}=10V$			
2N3019		$R_s=1K\Omega, f=1KHz$		4	dB
Collector Base Time Constant	$r_{bb'}cb'c$	$I_C=10mA, V_{CB}=10V, f=4MHz$		400	ps
		$f=1MHz$			

*Pulse Test: Pulse Width $\leq 300ms$, Duty Cycle $\leq 1.0\%$

2N3019
2N3020

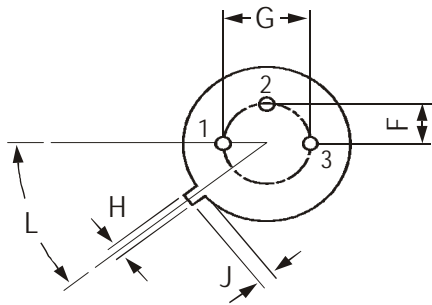
TO-39
Metal Can Package

TO-39 Metal Can Package



DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG

All dimensions are in mm



PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Datasheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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